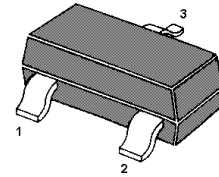
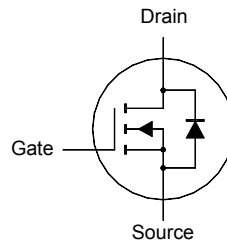


MMFTN170

N-Channel Enhancement Mode Field Effect Transistor

Feature

- Voltage controlled small signal switch
- High saturation current capability



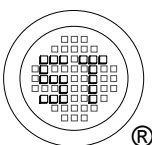
1. Gate 2. Source 3. Drain
SOT-23 Plastic Package

Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	60	V
Drain-Gate Voltage ($R_{GS} \leq 1\text{ M}\Omega$)	V_{DGR}	60	V
Gate-Source Voltage	V_{GSS}	± 20	V
Drain Current - Continuous	I_D	500	mA
Drain Current - Pulsed		800	
Total Power Dissipation	P_{tot}	300	mW
Operating and Storage Temperature Range	T_j, T_{stg}	- 55 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage at $I_D = 100\text{ }\mu\text{A}$	$V_{(BR)DSS}$	60	-	-	V
Zero Gate Voltage Drain Current at $V_{DS} = 25\text{ V}$	I_{DSS}	-	-	0.5	μA
Gate-Body Leakage, Forward at $V_{GS} = 15\text{ V}$	I_{GSSF}	-	-	10	nA
Gate-Source Threshold Voltage at $V_{DS} = V_{GS}, I_D = 1\text{ mA}$	$V_{GS(th)}$	0.8	-	3	V
Static Drain-Source On-Resistance at $V_{GS} = 10\text{ V}, I_D = 200\text{ mA}$	$R_{DS(on)}$	-	-	5	Ω
Forward Transconductance at $V_{DS} \geq 2 V_{DS(on)}, I_D = 200\text{ mA}$	g_{FS}	-	320	-	mS
Input Capacitance at $V_{DS} = 10\text{ V}, f = 1\text{ MHz}$	C_{iss}	-	-	40	pF
Output Capacitance at $V_{DS} = 10\text{ V}, f = 1\text{ MHz}$	C_{oss}	-	-	30	pF
Reverse Transfer Capacitance at $V_{DS} = 10\text{ V}, f = 1\text{ MHz}$	C_{rss}	-	-	10	pF
Turn-On Time at $V_{DD} = 25\text{ V}, I_D = 500\text{ mA}, V_{GS} = 10\text{ V}, R_{GEN} = 50\text{ }\Omega$	$t_{(on)}$	-	-	10	ns
Turn-Off Delay Time at $V_{DD} = 25\text{ V}, I_D = 500\text{ mA}, V_{GS} = 10\text{ V}, R_{GEN} = 50\text{ }\Omega$	$t_{(off)}$	-	-	10	ns



SEMTECH ELECTRONICS LTD.
Subsidiary of Sino-Tech International (BVI) Limited



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